

Terms and Symbols

A	closed-loop voltage gain	I _A	amplifier supply current	I _{OM}	peak output current
A _{AF}	audio amplifier gain	I _{ABC}	amplifier bias current	I _{OM}	magnitude of peak output current
A _{DIFF}	differential voltage gain	I _{AGC}	AGC source current	I _{OM} ⁺	maximum output current (source)
ACC	automatic chroma control	I _B	base current	I _{OM} ⁻	maximum output current (sink)
AFC	automatic frequency control	I _C	collector current	I _p	photo current
AFT	automatic fine tuning	I _{CB0}	collector cutoff current	I _{p-p}	peak-to-peak output current
AGC	automatic gain control	I _{CEO}	collector cutoff current	I _Q	total quiescent current
AMR	am rejection	I _{CE(OFF)}	output leakage current	I _{QPL}	charge-pump input current
AOL	open-loop voltage gain	I _D	drain current	I _R	dc reverse (leakage) current
A _V	amplifier voltage gain	I _{D(ON)}	dc on-state drain current	I _{REFO}	supply current for reference
b _{fs}	small-signal, common-source, forward transfer susceptance (imaginary part of corresponding admittance; see v_{fs})	I _{DARK}	dark current	I _{SSO}	strobe load current (V_{SS})
b _{is}	small-signal, common-source, input susceptance (imaginary part of corresponding admittance; see v_{is})	I _{DF}	diode forward current	I _{SXO}	supply current for supply voltage
b _{os}	small-signal, common-source, output susceptance (imaginary part of corresponding admittance; see v_{os})	I _{DDO}	supply current for drain supply voltage (V_{DD})	I _{TH}	threshold current
b _{rs}	small-signal, common-source, reverse transfer susceptance (imaginary part of corresponding admittance; see v_{rs})	I _{DS}	zero-gate (bias) drain current (dual-gate types)	I _{TOTAL}	total supply current
BW	bandwidth (unity gain)	I _{DSS}	zero-gate (bias) drain current (single-gate types)	k _N	normalized factor ($k_N = k_N/k_T$)
BW _{OL}	open-loop bandwidth	I _F	forward current	MAG	maximum available power gain
C _{BI}	base-to-substrate capacitance	I _G	channel (input) gate lead current	MUG	maximum useable power gain (unneutralized)
C _{CB}	collector-to-base capacitance	I _{GR}	channel (input) gate reverse current	NF	noise factor
C _{EB}	emitter-to-base capacitance	I _{GS}	gate terminal current (single-gate types)	PO	power output
C _{EXT}	external capacitance	I _{G1S}	gate-No. 1 terminal current	PD	device dissipation
C _{FB}	feedback capacitance	I _{G2S}	gate-No. 2 terminal current	PSRR	power supply rejection ratio
C _I	input capacitance	I _{GSSF}	gate-to-source forward leakage current, all other terminals shorted to source (dual-gate types).	r _{ds(off)}	small-signal drain-to-source off-state resistance
C _{iOS}	small-signal output capacitance	I _{G1SSF}	gate-No. 1 source forward leakage current, all other terminals shorted to source (dual-gate types).	r _{ds(on)}	static drain-to-source on-state resistance
C _{iS}	small-signal input capacitance	I _{G2SSF}	gate-No. 2-to-source forward leakage current, all other terminals shorted to source (dual-gate types).	R _{GS}	gate leakage-current resistance
C _{iSS}	small-signal, common-source short-circuit input capacitance	I _{GSSR}	gate-to-source reverse leakage current, all other terminals shorted to source (single-gate types).	R _O	output resistance
C _{I-O}	input-to-output capacitance; data in/out capacitance	I _{G1SSR}	gate-No. 1-to-source reverse leakage current, all other terminals shorted to source (dual-gate types).	R _o	low-frequency output resistance
CMMR	common-mode rejection ratio	I _{G2SSR}	gate-No. 2-to-source reverse leakage current, all other terminals shorted to source (dual-gate types).	r _i	small-signal output resistance
C _O	output capacitance	I _{GSSR}	gate-to-source reverse leakage current, all other terminals shorted to source (single-gate types).	r _{iss}	small-signal, short-circuit, common-source input resistance
C _{OS}	feedthrough capacitance	I _{G1SSR}	gate-No. 1-to-source reverse leakage current, all other terminals shorted to source (dual-gate types).	R _i	low-frequency input resistance
C _{OSS}	small-signal, common-source short-circuit output capacitance	I _{G2SSR}	gate-No. 2-to-source reverse leakage current, all other terminals shorted to source (dual-gate types).	R _{ON}	ON resistance; the ON-state resistance of an analog switch at specified input and load conditions.
C _{QP}	charge-pump capacitance	I _{GT}	gate trigger current; gate terminal current	ΔR _{ON}	ΔON resistance; the difference in ON-state resistance between any 2 analog switches at specified input and load conditions.
C _{rSS}	small-signal, common-source short-circuit, reverse transfer capacitance	I _I	input current	S/N	signal-to-noise ratio
e _i	input sensitivity	I _{IB}	input bias current	SR	slow rate
E _N	1/F noise voltage	I _{IBC}	internal bias current	T _A	ambient temperature
e _N	low-frequency noise voltage; equivalent short-circuit input noise voltage ($\mu V \sqrt{Hz}$)	I _{IO}	input offset current	t _d	delay time
e _{N(total)}	wideband noise voltage referenced to input	ΔI _{IO}	average temperature coefficient of input offset current	t _{DR}	differential recovery time
e _{O1} /e _{O2}	channel separation	ΔI _{IO} /ΔT	temperature coefficient of input offset current (drift)	t _f	fall time
E _{ON}	broadband output noise voltage	I _{LIM}	short-circuit limiting current	t _{fp}	input-pulse rise time
f _{CL}	clock input frequency	I _{MTR}	current-mirror transfer ratio	THD	total harmonic distortion
f _{max}	maximum operating frequency	I _N	1/F noise current	t _{off}	turn-off time
f _p	charge-pump input-pulse frequency	I _N	equivalent open-circuit noise current ($\mu A / \sqrt{Hz}$)	t _{on}	turn-on time
f _t	unity-gain crossover frequency; gain-bandwidth product	I _O	output current	t _r	rise time
f _{cp}	input-pulse frequency	I _{O(DIFF)}	differential output current (sink)	t _{Rφ}	input-pulse rise time
G _p	power gain	I _{OO}	output offset current	t _{rr}	reverse recovery time
G _m	forward transconductance (large-signal)		output leakage current, low	t _S	setup time
h _{FE}	static forward-current transfer ratio (beta)			t _{STG}	storage time
h _{fe}	small-signal forward-current transfer ratio			t _w	pulse width
I ⁺	dc supply current			V ⁺	DC positive supply voltage
I ⁻	dc supply current			V ⁻	DC negative supply voltage
				V _{ABC}	amplifier bias voltage
				V _{BB}	substrate voltage
				V _{BE}	base-to-emitter voltage

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$V_{BE(sat)}$	base-to-emitter saturation voltage	V_{G2S}	gate-No.2-to-source voltage (dual-gate types)	$ Y_{rs} $	magnitude of small-signal, common-source, short-circuit, reverse transadmittance
$V_{(BR)CBO}$	collector-to-base breakdown voltage	$V_{G2S(off)}$	gate-No.2-to-source cutoff voltage (dual-gate types)	$\angle Y_{rs}$	phase angle of small-signal, common-source, short-circuit, reverse transadmittance
$V_{(BR)CES}$	collector-to-emitter breakdown voltage	V_I	input voltage	$(-)_rs$	angle of reverse transadmittance, common-source circuit
$V_{(BR)DI}$	dc breakdown voltage between diode and substrate	$V_{I(Lim)}$	input limiting voltage	Z_I	input impedance
$V_{(BR)R}$	dc reverse breakdown voltage	V_{ICR}	common-mode input voltage range	Z_O	output impedance
$V_{(BR)EBO}$	emitter-to-base breakdown voltage	V_{IL}	input-voltage, low level	Z_Z	zener impedance
$V_{(BR)GSSF}$	dc gate-to-source forward breakdown voltage, all other terminals shorted to source (single-gate types)	V_{IH}	input-voltage, high level	ϕ	phase angle
$V_{(BR)G1SSF}$	dc gate-No.1-to-source forward breakdown voltage, all other terminals shorted to source (dual-gate types)	V_{IO}	input offset voltage	ϕ	phase margin
$V_{(BR)G2SSF}$	dc gate No.2-to-source forward breakdown voltage, all other terminals shorted to source (dual-gate types)	$ V_{IO} $	magnitude of input offset voltage	η	efficiency
$V_{(BR)GSSR}$	dc gate-to-source reverse breakdown voltage, all other terminals shorted to source (single-gate types)	$\Delta V_{IO}/\Delta T$	temperature coefficient of magnitude of input offset voltage	ϕ_L	open-loop phase lag
$V_{(BR)G2SSR}$	dc gate-No.2-to-source reverse breakdown voltage, all other terminals shorted to source (dual-gate types)	$\Delta V_{IO}/\Delta T$	temperature coefficient of input offset voltage drift		
V_{CBO}	collector-to-base voltage	$\Delta V_{IO}/\Delta V^+$	positive input-offset-voltage sensitivity		
V_{CC}	drain supply voltage used as a second positive supply voltage. It is $\leq V_{DD}$ and referenced to V_{SS}	$\Delta V_{IO}/\Delta V^-$	negative input-offset-voltage sensitivity		
V_{CO}	voltage controlled oscillator	aV_{IO}	average temperature coefficient of input-offset voltage		
V_{CEO}	collector-to-emitter voltage	$V_{i(Lim)}$	input limiting voltage (knee)		
$V_{CEO(sus)}$	collector-to-emitter sustaining voltage	V_{knee}	protective diode knee voltage (protected gate types)		
V_{C10}	collector-to-substrate voltage	V_N	output noise voltage		
V_{CP}	charge pump voltage	V_O	output voltage		
V_{DD}	drain supply voltage (the most positive supply voltage; always referenced to ground)	$\Delta V_{O}/\Delta V^-$	dc supply voltage sensitivity		
V_{DG}	drain-to-gate voltage (single-gate types)	$\Delta V_{O}/\Delta V^+$	dc supply voltage sensitivity		
V_{DG1}	drain-to-gate-No.1 voltage (dual-gate types)	$V_{O(rms)}$	open-loop output voltage swing		
V_{DG2}	drain-to-gate-No.2 voltage (single-gate types)	ΔV_O	output voltage temperature coefficient		
V_{DIO}	diode-to-substrate voltage	V_{Op-p}	output voltage swing		
V_{DR}	diode reverse voltage	$V_{O(af)}$	recovered af voltage		
V_{DS}	drain-to-source voltage	V_{OL}	output voltage, low level; the voltage level at an output when the input logic conditions have been set to establish logic LOW output.		
V_{EE}	source voltage (the most negative supply voltage in a 3-supply voltage system)	V_{OO}	output offset voltage		
V_F	dc forward voltage	V_{OH}	output voltage, high level; the voltage level at an output when the input logic conditions have been set to establish a logic HIGH output.		
$\Delta V_F/\Delta T$	temperature coefficient of forward voltage drop	V_{OM}^+	maximum output voltage		
V_{GH}	channel gate input voltage, high level	V_{OM}^-	maximum output voltage		
V_{GL}	channel gate input voltage, low level	V_{QP}	charge pump voltage		
V_{GS}	gate-to-source voltage	V_{QPL}	charge pump input voltage, low level		
$V_{GS(TH)}$	gate-to-source threshold voltage	V_{QPH}	charge-pump input voltage, high level		
$V_{GS(Off)}$	gate-to-source cutoff voltage (single-gate types)	V_{REF}	reference voltage		
V_{G1S}	gate-No.1-to-source voltage (dual-gate type)	V_{REG}	regulated supply voltage		
$V_{G1S(Off)}$	gate-No.1-to-source cutoff voltage (dual-gate types)	V_{RR}	supply voltage rejection ratio		
		V_{TH}	input threshold voltage		
		V_Z	zener voltage		
		Y_{fs}	magnitude of small-signal, common-source, short-circuit forward transfer admittance (transadmittance)		
		\bar{Y}_{is}	small-signal, common-source, short-circuit, input-admittance (conductance, real part of admittance; susceptance, imaginary part of admittance)		
		Y_{os}	small-signal, common-source, short-circuit, output admittance		